AON2705

30V P-Channel MOSFET with Schottky Diode

General Description

The AON2705 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. A Schottky diode is provided to facilitate the implementation of a bidirectional blocking switch, or for DC-DC conversion applications.

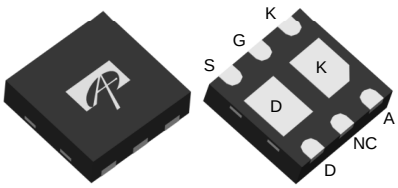
Product Summary

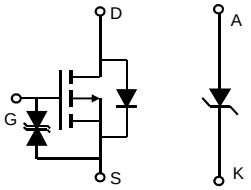
V_{DS}	-30V
I_D (at V_{GS}=-10V)	-3.0A
$R_{DS(ON)}$ (at V_{GS}=-10V)	< 108mΩ
$R_{DS(ON)}$ (at V_{GS} = -4.5V)	< 165mΩ
Typical ESD protection	**HBM Class 3A**
V_{KA}	20V
I_F	2A
V_F (at I_F=1A)	<0.45V

Green Product

DFN 2x2

Top View **Bottom View**





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	MOSFET	Schottky	Units
Drain-Source Voltage		V_{DS}	-30		V
Gate-Source Voltage		V_{GS}	±20		V
Continuous Drain Current [A]	T_A=25°C	I_D	-3		A
	T_A=70°C		-2.4		
Pulsed Drain Current [B]		I_{DM}	-16		
Schottky reverse voltage		V_{KA}		20	V
Continuous Forward Current [A]	T_A=25°C	I_F		2.5	A
	T_A=70°C			1.5	
Pulsed Forward Current [B]		I_{FM}		15	
Power Dissipation [A]	T_A=25°C	P_D	1.5	1.45	W
	T_A=70°C		0.95	0.92	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	-55 to 150	°C

Thermal Characteristics

Parameter: MOSFET		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	35	45	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		65	85	°C/W
Parameter: Schottky					
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	36	47	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		67	87	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-30V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±16V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250µA	-1.3	-1.8	-2.3	V
$I_{D(ON)}$	On state drain current	V_{GS}=-10V, V_{DS}=-5V	-16			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V, I_D=-3A		89	108	mΩ
		T_J=125°C		123	150	
		V_{GS}=-4.5V, I_D=-2.5A		132	165	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-3A		6		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.8	-1	V
I_S	Maximum Body-Diode Continuous Current				-1.25	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, f=1MHz		180		pF
C_{oss}	Output Capacitance			44		pF
C_{rss}	Reverse Transfer Capacitance			25		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		18.5	37	Ω
SWITCHING PARAMETERS						
$Q_{g(10V)}$	Total Gate Charge	V_{GS}=-10V, V_{DS}=-15V, I_D=-3A		4	6	nC
$Q_{g(4.5V)}$	Total Gate Charge			2	3.5	nC
Q_{gs}	Gate Source Charge			0.6		nC
Q_{gd}	Gate Drain Charge			1		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-10V, V_{DS}=-15V, R_L=5Ω, R_{GEN}=3Ω		8		ns
t_r	Turn-On Rise Time			5		ns
$t_{D(off)}$	Turn-Off DelayTime			18		ns
t_f	Turn-Off Fall Time			7		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-3A, dI/dt=100A/µs		10.5		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-3A, dI/dt=100A/µs		3.5		nC
SCHOTTKY PARAMETERS						
V_F	Forward Voltage Drop	I_F=1A		0.4	0.45	V
I_{rm}	Maximum reverse leakage current	V_R=5V			0.05	mA
		V_R=5V, T_J=125°C			10	
I_{rm}	Maximum reverse leakage current	V_R=16V			0.1	mA
		V_R=16V, T_J=125°C			20	
C_T	Junction Capacitance	V_R=10V		34		pF
t_{rr}	Schottky Reverse Recovery Time	I_F=1A, dI/dt=100A/µs		11	14	ns
Q_{rr}	Schottky Reverse Recovery Charge	I_F=1A, dI/dt=100A/µs		0.8		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.
B: Repetitive rating, pulse width limited by junction temperature.
C. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.
D. The static characteristics in Figures 1 to 6 are obtained using <300 ms pulses, duty cycle 0.5% max.
E. These tests are performed with the device mounted on 1 in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C. The SOA curve provides a single pulse rating.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

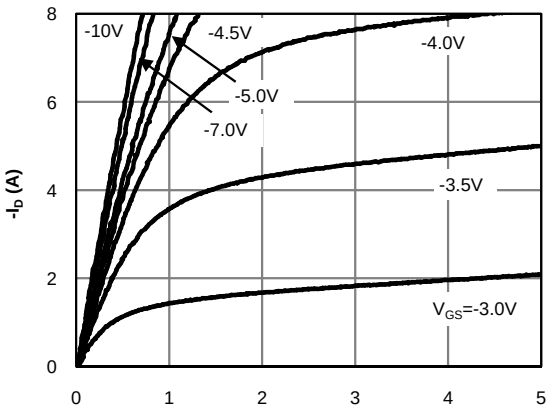


Fig 1: On-Region Characteristics

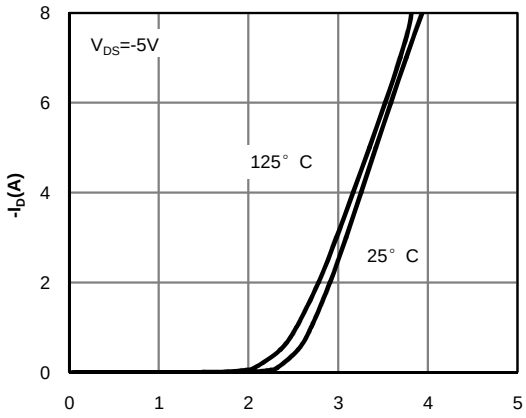


Figure 2: Transfer Characteristics

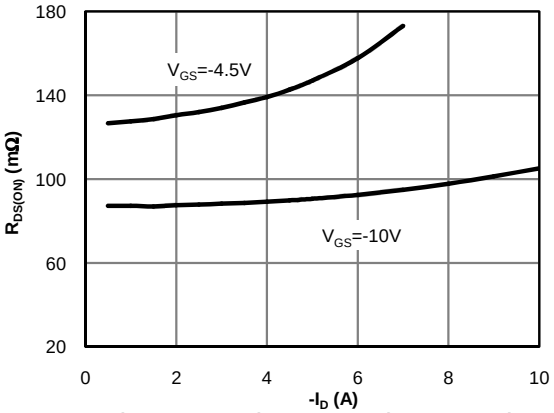


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

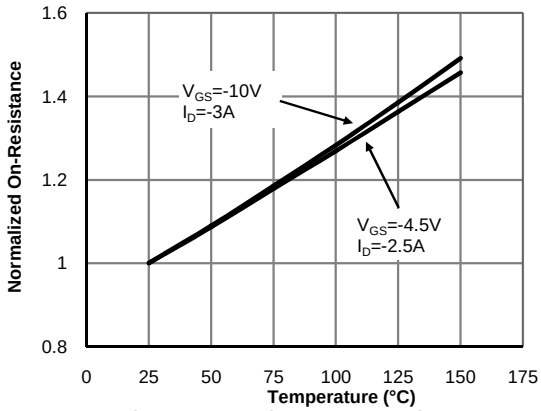


Figure 4: On-Resistance vs. Junction Temperature

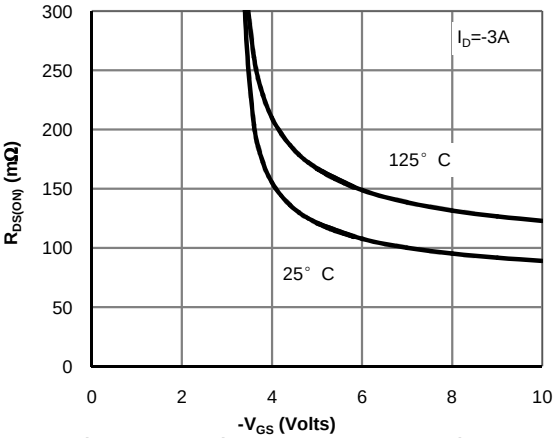


Figure 5: On-Resistance vs. Gate-Source Voltage

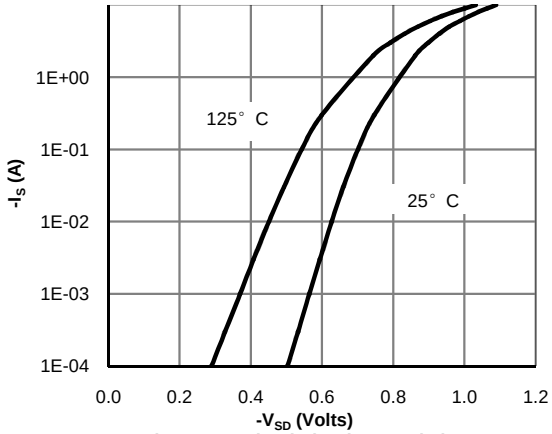


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

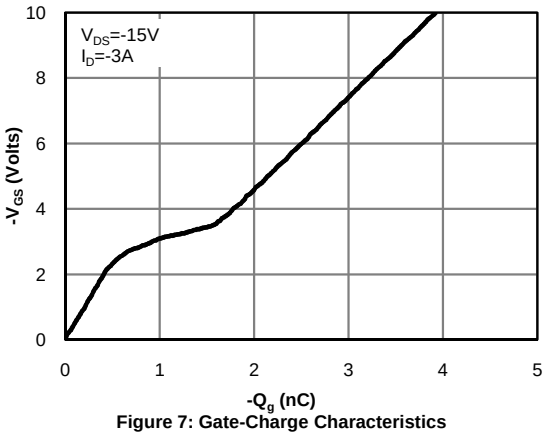


Figure 7: Gate-Charge Characteristics

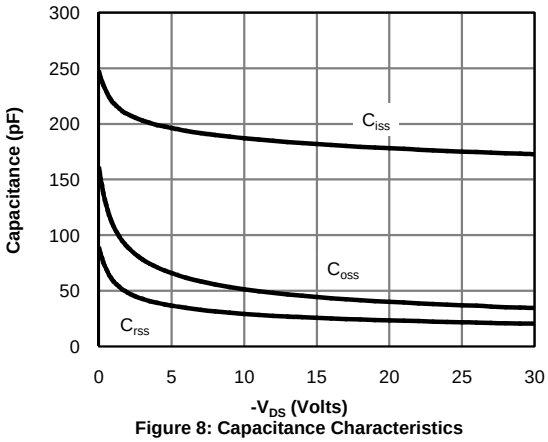


Figure 8: Capacitance Characteristics

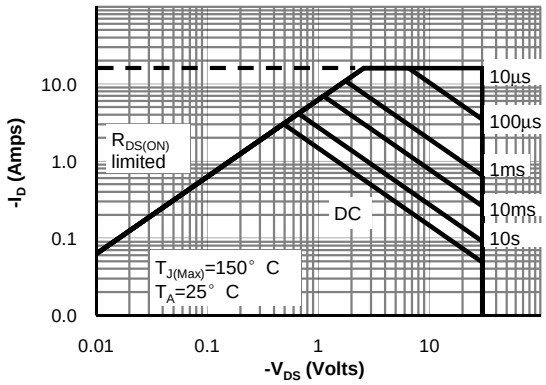


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

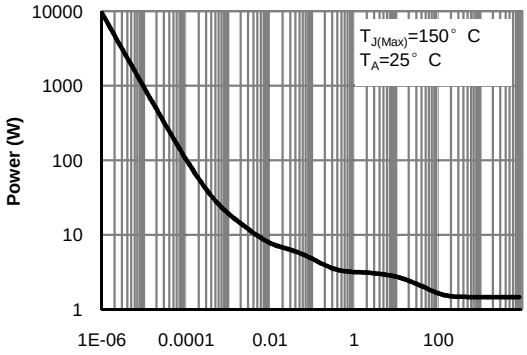


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

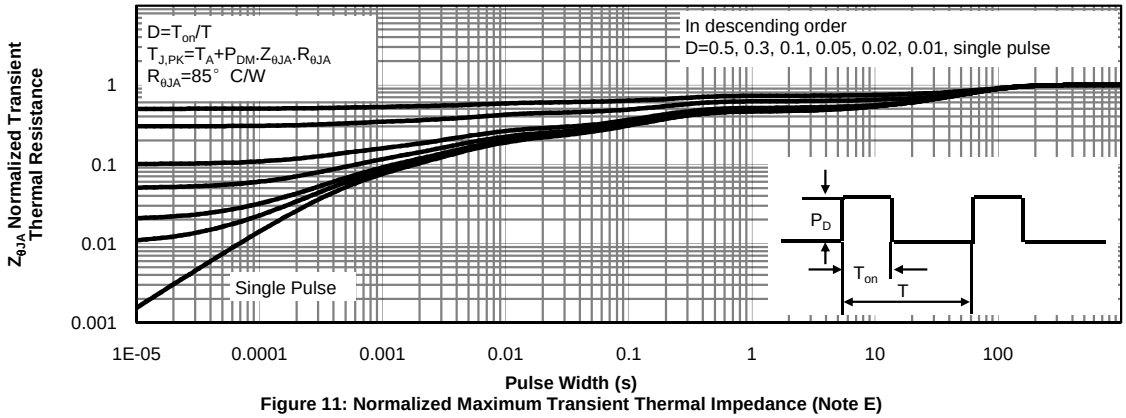


Figure 11: Normalized Maximum Transient Thermal Impedance (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

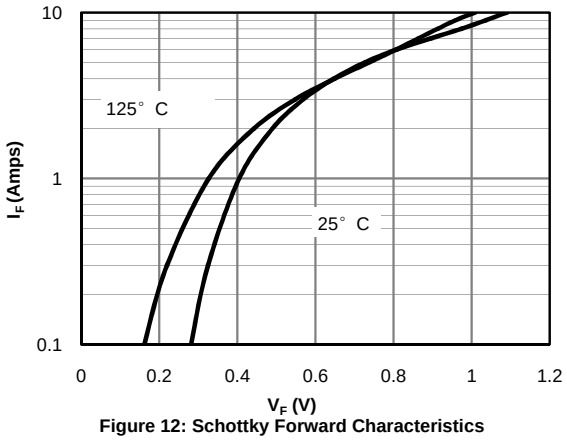


Figure 12: Schottky Forward Characteristics

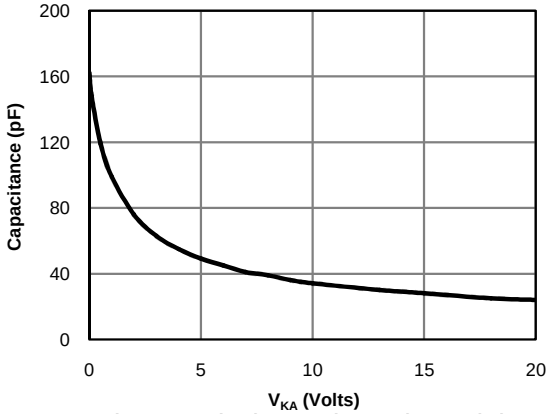


Figure 13: Schottky Capacitance Characteristics

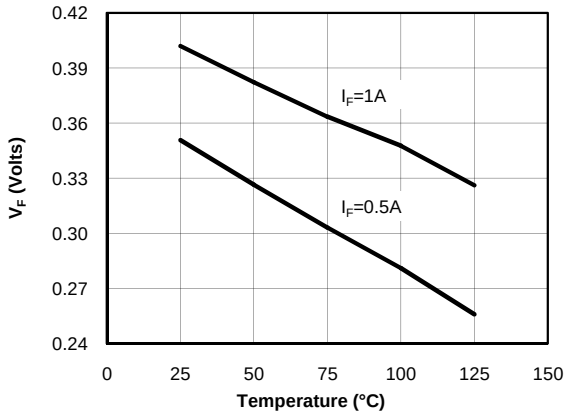


Figure 14: Schottky Forward Drop vs. Junction Temperature

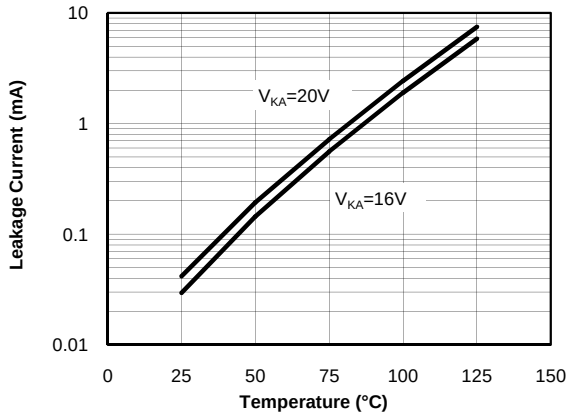


Figure 15: Schottky Leakage Current vs. Junction Temperature

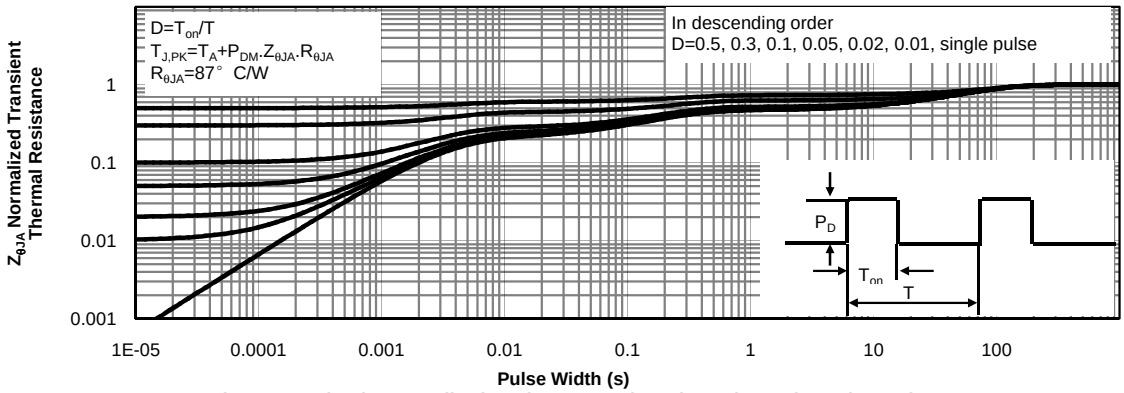
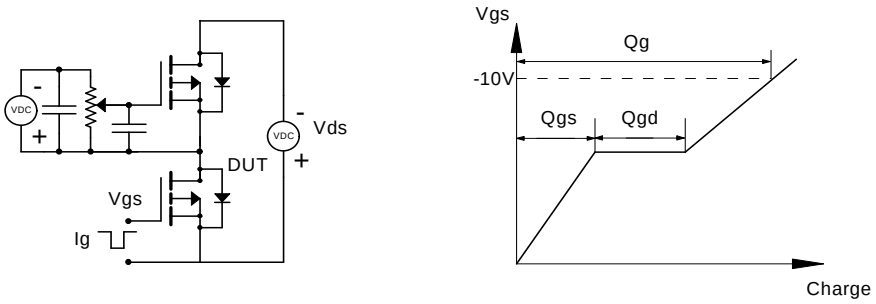
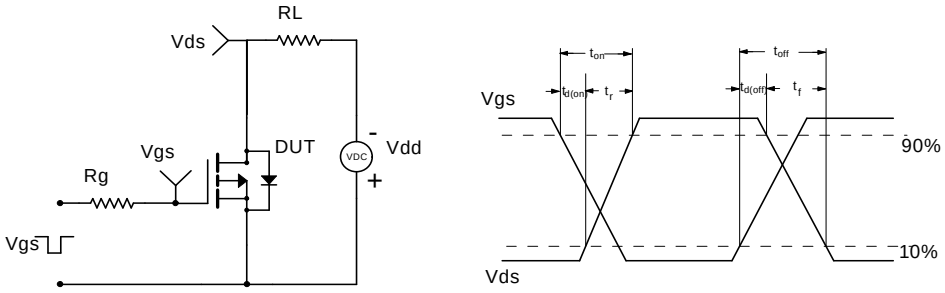


Figure 16: Schottky Normalized Maximum Transient Thermal Impedance (Note E)

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms